



500 μ m Si APD

(P/N.: ASi-500-01-01)

Features

- 500 μ m active area
- Low breakdown voltage <180V

Absolute Maximum Ratings

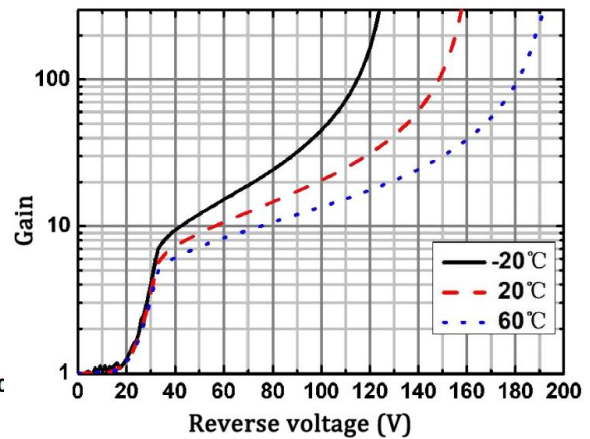
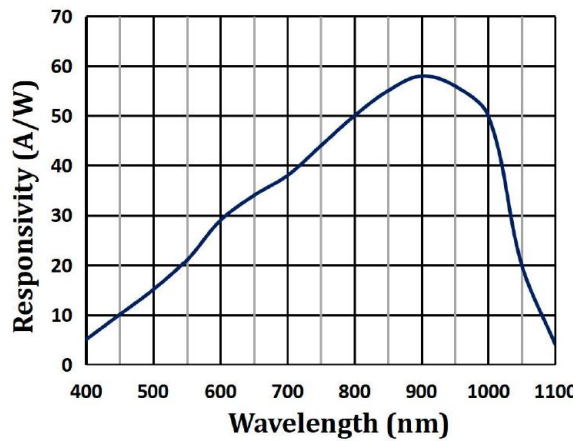
Parameter	Symbol	Min	Typ	Max	Unit
Operating Case Temperature	T _C	-40	-	85	°C
Storage Temperature	T _{STG}	-55	-	85	°C

Opto-Electrical Characteristics

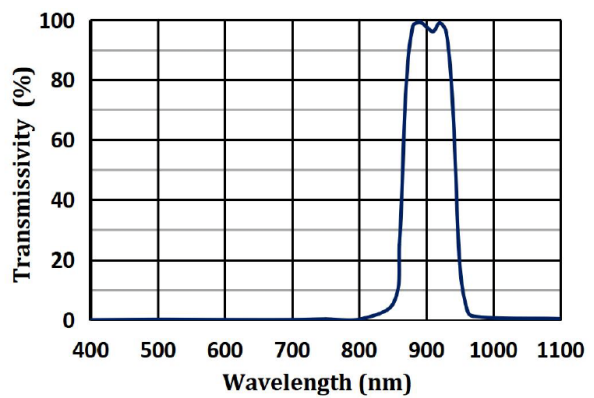
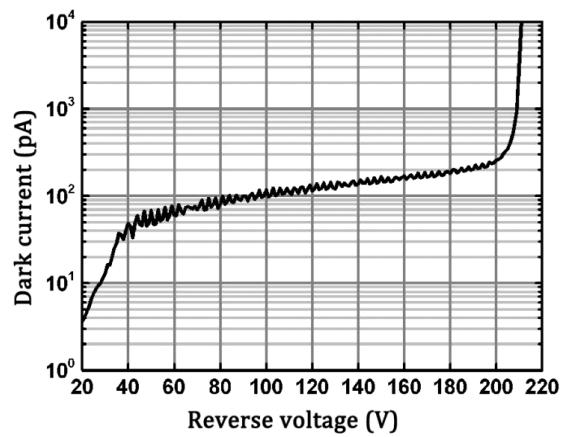
Parameter	Symbol	Min	Typ	Max	Unit	Notes
Wavelength Range	λ	400		1100	nm	
Reverse Breakdown Voltage	V _{BR}	130	180	220	V	I _D = 100 μ A
Risetime (@ 905nm)	τ_{rise}	-	0.6	-	V	50Ohm, M = 100
Spectral Responsivity	S	-	0.55	-	A/W	905nm, M = 1
Multiplied Dark Current	I _{DM}	-	0.4	1	nA	M = 100
Terminal Capacitance	C _J	-	1.1	1.2	pF	M = 100
Temperature coeff of V _{BR}	$\Delta V/\Delta T$	-	1.1	-	V/°C	T = 25°C



Responsivity and gain performances



Dark current and responsivity with a filter option



Dimensional outlines (unit = mm)

TO

Package can be customized

